Unit

v

V

V A (DC)

A (Pulse)

W

°C

°C

\*1

\*2

\*3

# Power Transistor (-50V, -2A)

2SA1797 / 2SB1443

### Features

- 1 ) Low saturation voltage,  $V_{CE(sat)} = -0.35V(Max.)$  at Ic / IB=-1A / -50mA.
- 2  $\rangle\,$  Excellent DC current gain characteristics.
- 3 ) Complements the 2SA1797 and 2SC4672.

### Packaging specifications and hre

Туре	2SA1797	2SB1443
Package	MPT3	ATV
hfe	PQ	q
Marking	AG*	_
Code	T100	TV2
Basic ordering unit (pieces)	1000	2500

\* Denotes hre

### ●Electrical characteristics (Ta=25℃)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage BVcBo		ВУсво	-50	—	-	V	$lc = -50 \mu A$	
Collector-emitter breakdown voltage		BVCEO	-50	—	- 1	V	Ic=-1mA	
Emitter-base breakdown	voltage	BVево	-6	—	—	V	IE=-50 μ A	
Collector cutoff current		Ісво	—	—	-0.1	μA	V <sub>CB</sub> =-50V	
Emitter cutoff current		Іево	-	—	-0.1	μA	VEB=-5V	
Collector-emitter saturation voltage		VCE(sat)	—	-0.15	-0.35	V	Ic/IB=-1A/-50mA	*
DC current transfer ratio	2SA1797		82	—	270	—		
	2SB1443	hfe	120	—	270	—	Vce/lc=-2V/-0.5A	
Transition frequency		fт	—	200	—	MHz	Vce=-2V, le=0.5A, f=100MHz	*
Output capacitance		Cob	—	36	_	pF	V <sub>CB</sub> =-10V, I <sub>E</sub> =0A, f=1MHz	

\* Measured using pulse current.

(96-100-B208)

# Low Frequency Transistor (50V, 2A) 2SC4672

### Features

- 1) Low saturation voltage, typically VCE(sat) =0.1V at Ic / IB=1A / 50mA.
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SA1797.

### Packaging specifications and hre

Туре	2SC4672
Package	MPT3
hfe	PQ
Marking	DK*
Code	T100
Basic ordering unit (pieces)	1000

\* Denotes hre

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	60	—	—	V	Ic=50 μ A	
Collector-emitter breakdown voltage	BVCEO	50	—	—	V	Ic=1mA	
Emitter-base breakdown voltage	ВVево	6	—	—	V	IE=50 μ A	
Collector cutoff current	Ісво	—	—	0.1	μA	Vcb=60V	
Emitter cutoff current	Іево	—	—	0.1	μA	VEB=5V	
Collector-emitter saturation voltage	VCE(sat)	—	0.1	0.35	V	Ic/IB=1A/50mA	*
DC current transfer ratio	hfe	82	—	270	—	VcE=2V, Ic=0.5A	*
Transition frequency	fт	—	210	—	MHz	Vce=2V, Ie=-0.5A, f=100MHz	
Output capacitance	Cob	—	25	—	pF	VCB=10V, IE=0A, f=1MHz	

\* Measured using pulse current.

### ●Absolute maximum ratings (Ta=25℃)

Absolute maximum ratings (Ta=25°C)

2SA1797

2SB1443

\*2 When mounted on a 40×40×0.7mm ceramic board.
\*3 Printed circuit board 1.7mm thick, collector plating 1cm<sup>2</sup> or larger.

Symbol

Vсво

VCEO

Vево

lc

Pc

Tj

Tstg

Limits

-50

-50

-6

-2

-5

0.5

2

1

150

55~+150

Parameter

Collector-base voltage

Emitter-base voltage

Junction temperature

Storage temperature

\*1 Single pulse Pw=10ms

Collector current

Collector power

dissipation

Collector-emitter voltage

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	60	V	
Collector-emitter voltage	VCEO	50	V	
Emitter-base voltage	VEBO	6	V	
Collector current		2	A (DC)	
	lc	5	A (Pulse)	*
Collector power dissipation	Pc	0.5	W	
Junction temperature	Tj	150	Ĵ	
Storage temperature	Tstg	-55~+150	Ĵ	

\* Single pulse, Pw=10ms



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